Dec 2013

SemiHow
Know-How for Semiconductor

HCD7NE70S

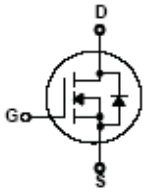
700V N-Channel Super Junction MOSFET

BV_{DSS} = 700 V
$R_{DS(on)\ typ}$ = 0.95 Ω
I_D = 6.0 A

D-PAK



1.Gate 2. Drain 3. Source



FEATURES

- ❑ Originative New Design
- ❑ Superior Avalanche Rugged Technology
- ❑ Robust Gate Oxide Technology
- ❑ Very Low Intrinsic Capacitances
- ❑ Excellent Switching Characteristics
- ❑ Unrivalled Gate Charge : 9 nC (Typ.)
- ❑ Extended Safe Operating Area
- ❑ Lower $R_{DS(ON)}$: 0.95 Ω (Typ.) @V_{GS}=10V
- ❑ 100% Avalanche Tested

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter		Value	Units
V_{DSS}	Drain-Source Voltage		700	V
I_D	Drain Current – Continuous (T_C = 25℃)		6.0	A
	Drain Current – Continuous (T_C = 100℃)		3.8	A
I_{DM}	Drain Current – Pulsed (Note 1)		15.6	A
V_{GS}	Gate-Source Voltage	Static	±20	V
		AC (f>1 Hz)	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		40	mJ
I_{AR}	Avalanche Current (Note 1)		1.2	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		0.1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		50	V/ns
P_D	Power Dissipation (T_A = 25℃)*		2.1	W
	Power Dissipation (T_C = 25℃)		28	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	℃

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	4.4	℃/W
$R_{\theta JA}$	Junction-to-Ambient*	--	60.5	
T_{sold}	Soldering temperature, wave soldering only allowed at leads	--	260	℃

* When mounted on the minimum pad size recommended (PCB Mount)

◎ SEMIHOW REV.A0, Dec 2013

Package Marking and Odering Information

Device Marking	Week Marking	Package	Packing	Quantity	RoHS Status
HCD7NE70S	YWWX	TO-251	Tube / Reel	80 / 2,500	Pb Free
HCD7NE70S	YWWXg	TO-251	Tube / Reel	80 / 2,500	Halogen Free

Electrical Characteristics T_J=25 °C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.5	--	4.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 2.3 A	--	0.95	1.1	Ω
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	700	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 700 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 560 V, T_J = 125℃	--	--	10	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	--	--	±100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V, f = 1.0 MHz	--	340	440	pF
C_{oss}	Output Capacitance		--	20	26	pF
C_{rss}	Reverse Transfer Capacitance		--	5.0	6.5	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 350 V, I_D = 2.3 A, R_G = 10 Ω (Note 4,5)	--	20	50	ns
t_r	Turn-On Rise Time		--	25	60	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Turn-Off Fall Time		--	30	70	ns
Q_g	Total Gate Charge	V_{DS} = 560 V, I_D = 2.3 A V_{GS} = 10 V (Note 4,5)	--	9.0	12	nC
Q_{gs}	Gate-Source Charge		--	2.0	--	nC
Q_{gd}	Gate-Drain Charge		--	3.0	--	nC
$V_{plateau}$	Gate-Plateau Voltage		--	5.0	--	V
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	6.0	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	15.2	
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 2.3 A, V_{GS} = 0 V	--	--	1.2	V
trr	Reverse Recovery Time	I_S = 2.3 A, V_{GS} = 0 V di_F/dt = 100 A/μs (Note 4)	--	150	--	ns
Qrr	Reverse Recovery Charge		--	1.1	--	μC
Irrm	Peak Reverse Recovery Current		--	12	--	A

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L=15mH, I_{AS}=2.3A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
3. I_{SD}≤6.0A, di/dt≤200A/μs, V_{DD}≤BV_{DSS} , Starting T_J=25 °C
4. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature

Typical Characteristics

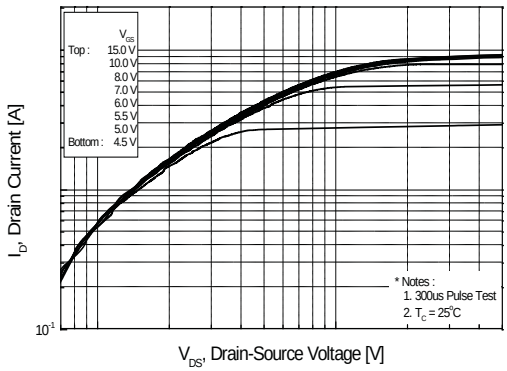


Figure 1. On Region Characteristics

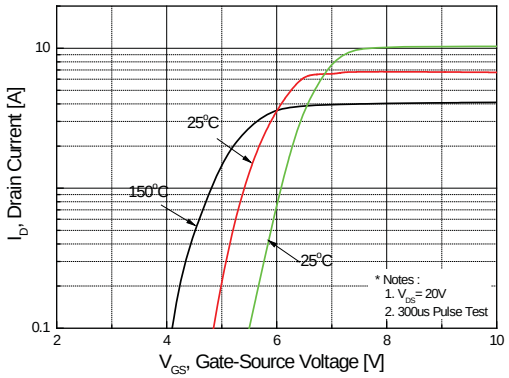


Figure 2. Transfer Characteristics

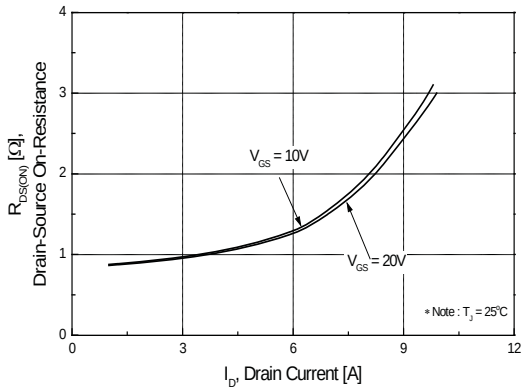


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

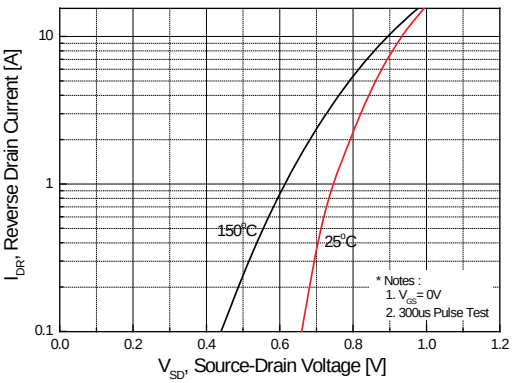


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

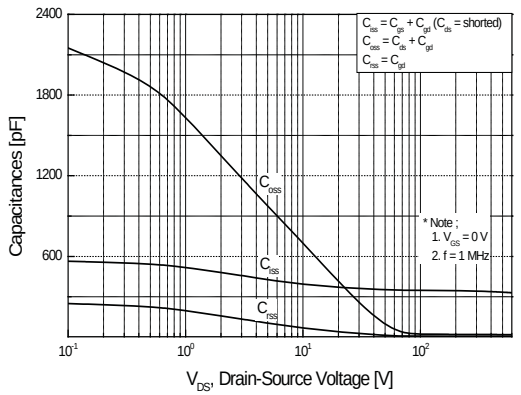


Figure 5. Capacitance Characteristics

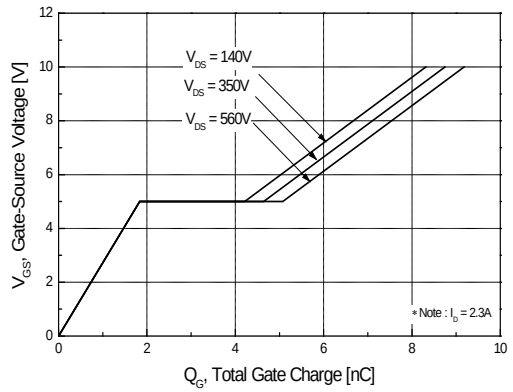


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

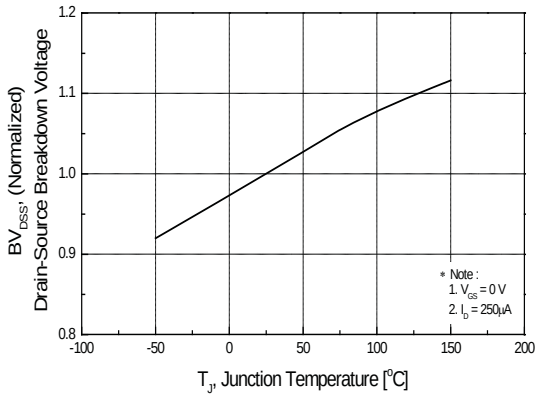


Figure 7. Breakdown Voltage Variation vs Temperature

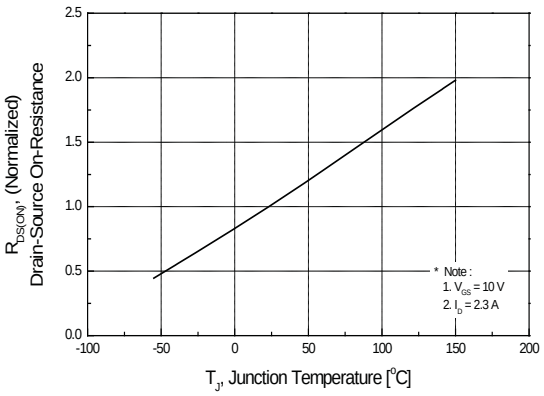


Figure 8. On-Resistance Variation vs Temperature

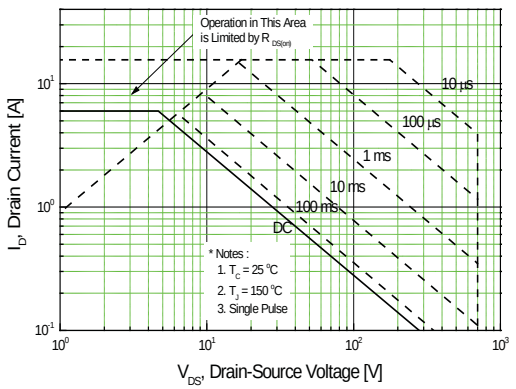


Figure 9. Maximum Safe Operating Area

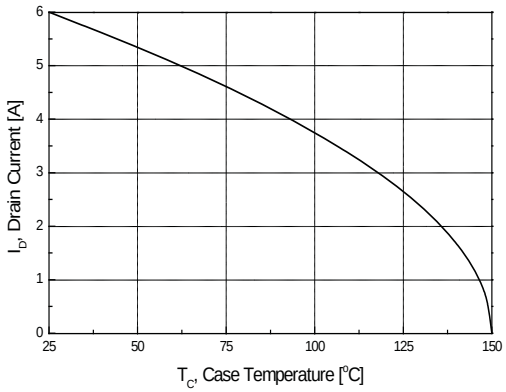


Figure 10. Maximum Drain Current vs Case Temperature

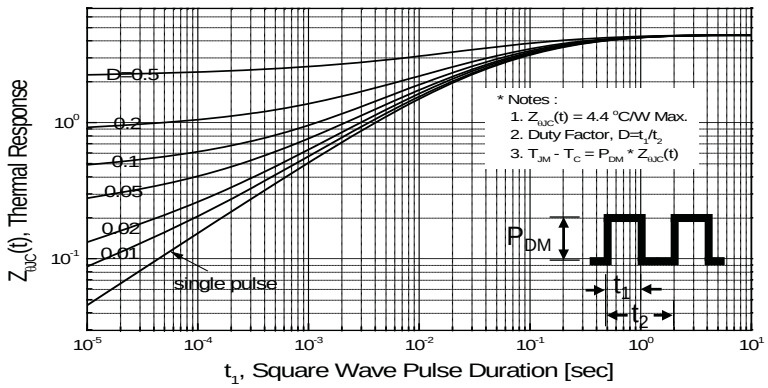


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

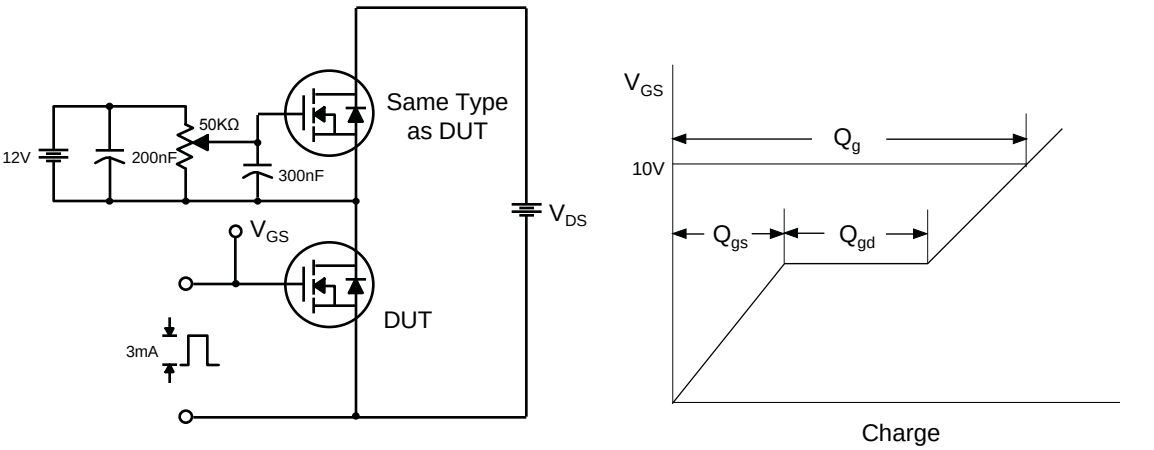


Fig 13. Resistive Switching Test Circuit & Waveforms

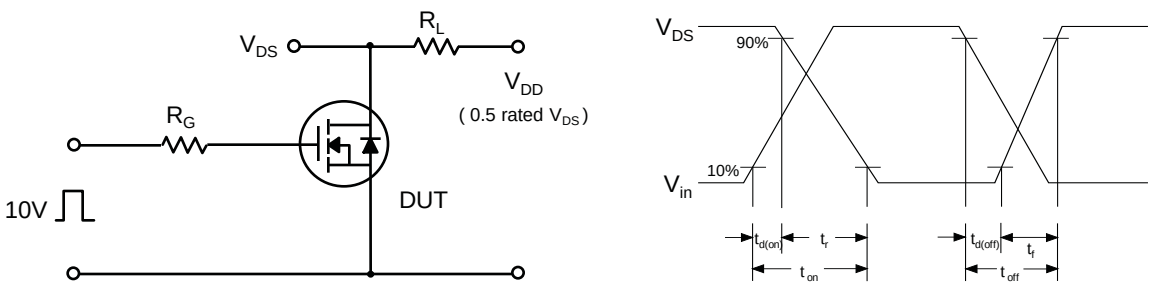


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

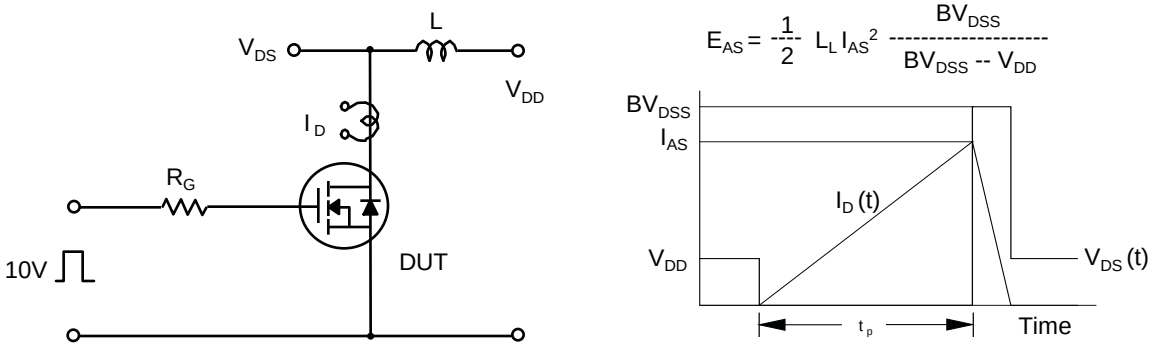
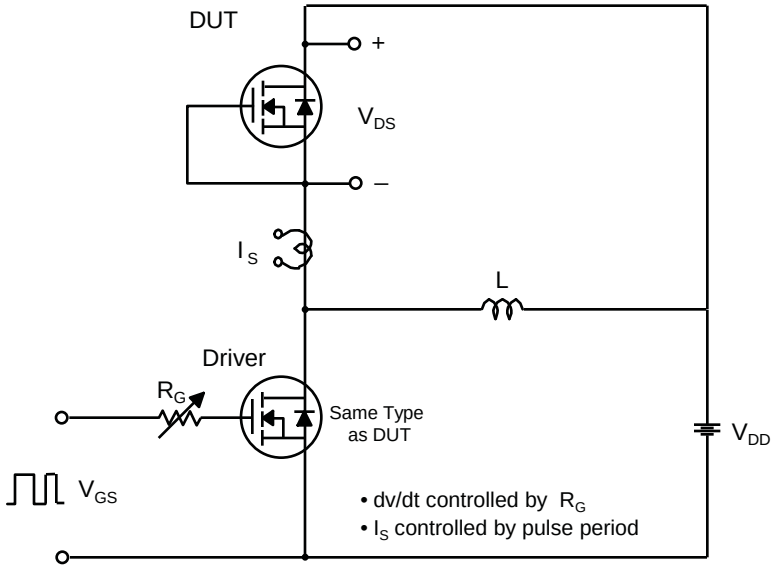
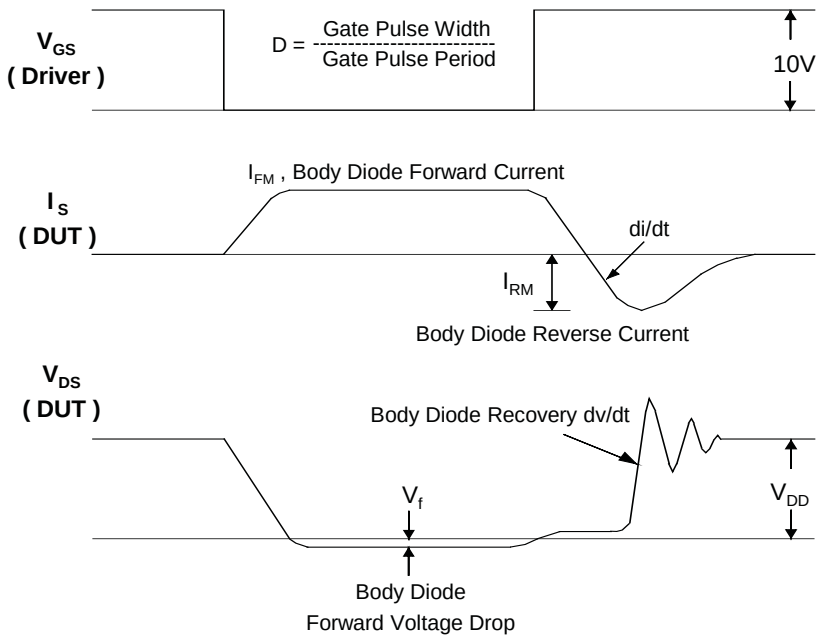


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Dimension

TO-252

